## NSN 5961-01-116-4492

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-116-4492 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.165 inches **Terminal Length:** Between 1.000 inches and 1.250 inches **Overall Diameter:** Between 0.085 inches and 0.140 inches **End Application:** B-52 weapon sys 36378 **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 210.0 breakdown voltage, dc **Current Rating Per Characteristic:** 5.00 milliamperes forward current, total rms nanoamperes **Power Rating Per Characteristic:** 500.0 watts small-signal input power, common-collector of standard range **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Precious Material And Location:** Terminal surfaces gold **Precious Material:** 

Gold

## **Test Data Document:**

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

## **Terminal Type And Quantity:**

2 uninsulated wire lead

**Specification Data:** 

81349-mil-s-19500/516 government specification

Shelf Life:

N/a

**Unit Of Measure:** 

**Demilitarization:** 

No

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